TOSHIBA TRANSISTOR SILICON NPN EPITAXIAL TYPE (PCT PROCESS)

# 2 S C 2 7 0 3

## **AUDIO POWER AMPLIFIER APPLICATIONS**

• High DC Current Gain: hFE=100~320

## MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V <sub>CBO</sub>	30	V
Collector-Emitter Voltage	VCEO	30	V
Emitter-Base Voltage	$V_{ m EBO}$	5	V
Collector Current	$I_{\mathbf{C}}$	1	Α
Base Current	$I_{B}$	0.1	A
Collector Power Dissipation	PC	900	mW
Junction Temperature	$T_{j}$	150	°C
Storage Temperature Range	$\mathrm{T_{stg}}$	-55~150	°C

# Unit in mm 5.1 MAX. 0.75MAX. 1.0MAX. 0.8MAX. 0.6MAX. 1.27 1

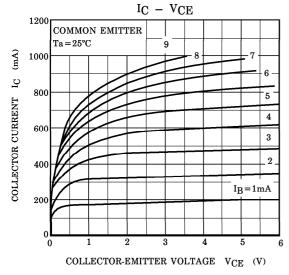
Weight: 0.36g (Typ.)

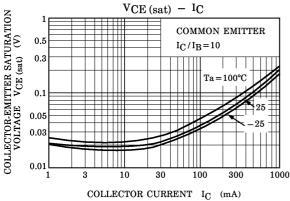
## ELECTRICAL CHARACTERISTICS (Ta = 25°C)

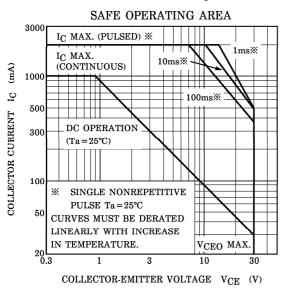
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I <sub>CBO</sub>	$V_{CB} = 30V, I_{E} = 0$	_	_	100	nA
Emitter Cut-off Current	I <sub>EBO</sub>	$V_{EB}=5V, I_{C}=0$	_	_	100	nA
Collector-Emitter Breakdown Voltage	V (BR) CEO	$I_{\rm C}=10{\rm mA},~I_{\rm B}=0$	30	_	_	V
DC Current Gain	hFE (1) (Note)	V <sub>CE</sub> =2V, I <sub>C</sub> =100mA	100	_	320	
	hFE (2)	$V_{\text{CE}} = 2V, I_{\text{C}} = 800 \text{mA}$	40	_	_	
Collector-Emitter Saturation Voltage	V <sub>CE</sub> (sat)	I <sub>C</sub> =800mA, I <sub>B</sub> =80mA	_	_	0.5	V
Base-Emitter Voltage	$V_{ m BE}$	$V_{CE} = 2V, I_{C} = 800 \text{mA}$	_	0.9	1.5	V
Transition Frequency	$ m f_{T}$	$V_{CE} = 2V, I_{C} = 100 \text{mA}$	_	150	_	MHz
Collector Output Capacitance	$C_{ob}$	$V_{CB} = 10V, I_{E} = 0, f = 1MHz$	_	13	_	pF

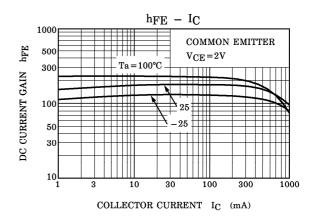
(Note) :  $h_{FE(1)}$  Classification  $O: 100\sim200, Y: 160\sim320$ 

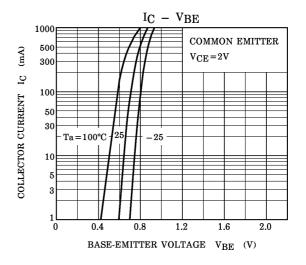
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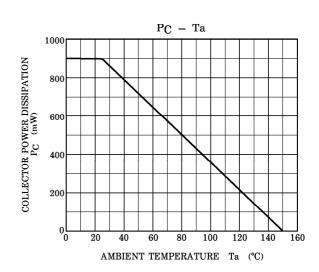












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